



# **Product Specification**

Domestic Part Number	IPD50P03P4L-11
Overseas Part Number	IPD50P03P4L-11
Equivalent Part Number	IPD50P03P4L-11



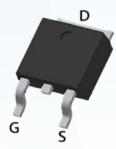
$V_{\text{DSS}} \ (v)$	Rds (on)	D(A)
-30	8.2mΩ(Typ)@VGS=-10V	-60
	17mΩ(Typ)@VGS=-4.5V	-60

### FEATURE:

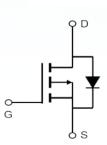
• The IPD50P03P4L-11 is the high cell density trenched P-ch MOSFETS, which provides excellent RDSON and efficiency for most of the small power switching and load switch applications.

- ★ 100% EAS Guaranteed
- $\star$  Green Device Available
- ★ Super Low Gate Charge
- ★Excellent CdV/dt effect decline
- ★Advanced high cell density Trench technology

**Pin Description** 



TO-252



# Absolute Maximum Ratings

Symbol	Parameter			Units	
VDSS	Drain-Source Voltage			V	
Vgss	Gate-Source Voltage		±20	V	
	Continuous Drain Current(V <sub>GS=</sub> -4.5V)	Tc=25°C	-60	А	
D		Tc=70°C	-32		
TJ	Maximum Junction Temperature			°C	
Тѕтд	Storage Temperature Range			°C	
Ідм	Pulsed Drain Current		-150	А	
D-	Maximum Dawas Diasis stian	Tc=25°C	45	10/	
PD	Maximum Power Dissipation	Tc=70°C		W	
Eas	Avalanche Energy, Single Pulse	125	mJ		
RθJC	Thermal Resistance-Junction to Case			°C/W	
RθJA	Thermal Resistance-Junction to Ambient		62	°C/W	

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit	
Static C	haracteristics						
BVDSS	Drain-Source Breakdown Voltage	VGS=0V, ID=250uA	-30			V	
VGS(th)	Gate threshold voltage	VDS=VGS,ID=250uA	-1.0	-1.6	-2.5	V	
	Desire Oscara Oscarata Desistence	VGS=-10V , ID=-10A		8.2	14	mΩ	
RDS(ON)	Drain-Source On-state Resistance	VGS=-4.5V , ID=-5A		17	24	mΩ	
IGSS	Gate-source leakage current	VGS=±20V , VDS=0V			±100	nA	
		VDS=-30V,VGS=0V,TJ=25℃			-1	-	
IDSS	Zero gate voltage drain current	<b>TJ=55</b> ℃				μA	
Dynami	c Characteristic				<u> </u>		
Ciss	Input Capacitance			1770			
Coss	Output Capacitance	VGS=0V, VDS=-15V, Frequency=1.0MHz		233		pF	
Crss	Reverse Transfer Capacitance			206			
QG	Gate Total Charge			22		nC	
Qgs	Gate-Source charge			1.0			
Qgd	Gate-Drain charge			1.8			
td(on)	Turn-on delay time			9			
tr	Turn-on Rise Time	VDD=-15V , VGS=-10V ,		13			
td(off)	Turn-off Delay Time	RG=2.5Ω, ID=-10A		48		ns	
tf	Turn-off Fall Time			20			
RG	Gate Resistance	VGS=0V,VDS=0V,F=1MHz		9		Ω	
Diode C	haracteristics						
VSD	Diode Forward Voltage	VGS=0V , IS=1A , TJ=25℃			-1.2	V	
ls	Maximum Continuous Drain to Source Diode Forward Current				-15	А	
lsм	Maximum Pulsed Drain to Source Diode Forward Current				-60	А	
trr	Reverse Recovery Time	ISD=-2.8A,		64		ns	
Qrr	Reverse Recovery Charge	dISD/dt=-100A/µs		25		nC	

Electrical Characteristics (TA=25°C Unless Otherwise Noted)

# TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

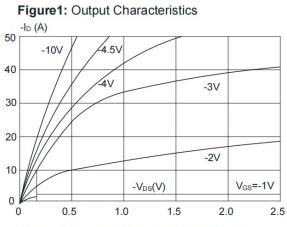
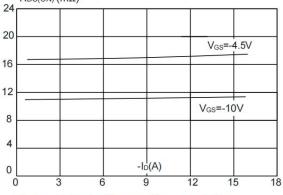
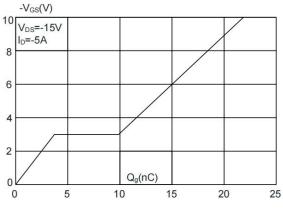


Figure 3: On-resistance vs. Drain Current

RDS(ON) ( $m\Omega$ )







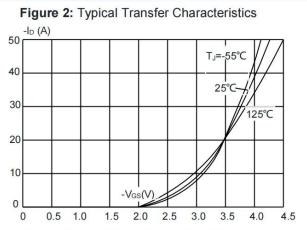
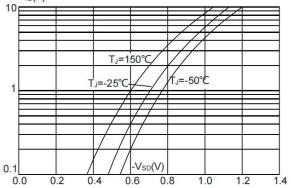
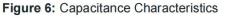
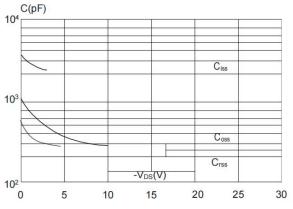


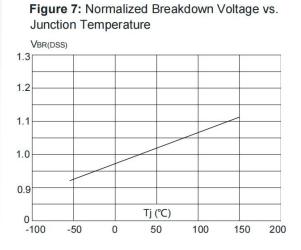
Figure 4: Body Diode Characteristics













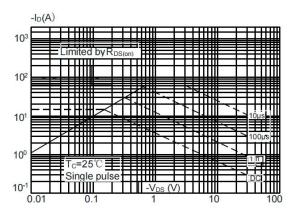
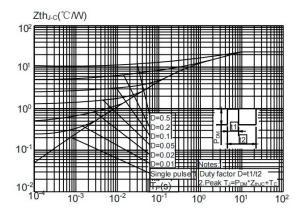
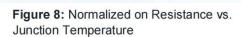


Figure.11: Maximum Effective Transient Thermal Impedance, Junction-to-Case





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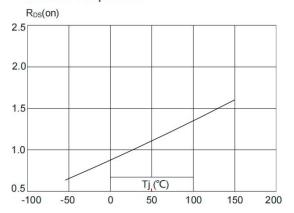
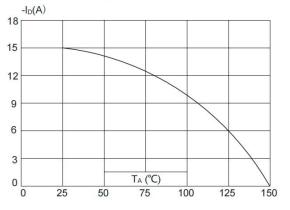
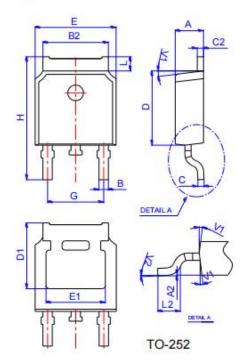


Figure 10: Maximum Continuous Drain Current vs. Ambient Temperature



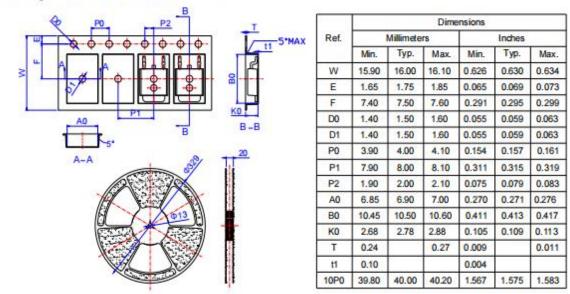


#### Package Mechanical Data:TO-252-3L



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Тур.	Max.	Min.	Тур.	Max
А	2.10		2.50	0.083		0.098
A2	0	1	0.10	0		0.004
В	0.66		0.86	0.026		0.034
B2	5.18		5.48	0.202		0.216
С	0.40	8	0.60	0.016		0.024
C2	0.44	0	0.58	0.017		0.023
D	5.90		6.30	0.232		0.248
D1	5.30REF			0.209REF		
E	6.40	24 	6.80	0.252		0.268
E1	4.63			0.182		
G	4.47	1	4.67	0.176		0.184
н	9.50		10.70	0.374		0.421
L	1.09		1.21	0.043		0.048
L2	1.35		1.65	0.053	: 	0.065
V1		7°	1		7°	
V2	0°		6°	0°		6°

#### **Reel Spectification-TO-252**





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